

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND**  
**CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

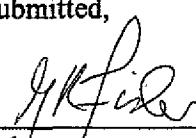
*Customer Number: 76681*

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

*Customer Number: 76681*

Respectfully submitted,

Date: 5/13/2008

  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**STATEMENT UNDER 37 CFR 3.73(b)**

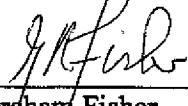
***MEMC Electronic Materials, Inc.***, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property***, has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008

  
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Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

**APPENDIX A**  
**Owned by MEMC Electronic Materials, Inc.**

| ATTORNEY<br>REFERENCE     | CONF. NO | PUBLICATION NO. &<br>DATE         | SERIAL NO.<br>FILING DATE  | PATENT NO.<br>ISSUE DATE           | CURRENT OWNER/<br>ASSIGNEE                            | REEL AND FRAME<br>NO. | TITLE  |
|---------------------------|----------|-----------------------------------|----------------------------|------------------------------------|---|-----------------------|--|
| 28744215<br>(MEMC2905.16) | 4312     | US2007-0169683-A1<br>7/26/2007    | 11/16/23/442<br>1/15/2007  | MEMC Electronic<br>Materials, Inc. | Division of 10/390,816<br>recorded at<br>014339/083/2 |                       | NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF<br>OXIDATION INDUCED STACKING FAULTS  |
| MEMC2905.9                | 1990     | US-2004-000911-A1<br>1/15/2004    | 10/380,806<br>7/30/2003    | MEMC Electronic<br>Materials, Inc. | 014339/083/2  |                       | NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF<br>OXIDATION INDUCED STACKING FAULTS  |
| MEMC2907.1                | 3830     | US-2003-007963-A1<br>5/17/2003    | 10/23/16/2<br>10/28/2002   | MEMC Electronic<br>Materials, Inc. | 013562/0432   |                       | SEED CRYSTALS FOR PULLING SINGLE CRYSTAL SILICON   |
| MEMC2960.1                | 5778     | US-2002-010040-A1<br>8/12/2002    | 10/03/4,629<br>1/22/2002   | MEMC Electronic<br>Materials, Inc. | 012789/0747   |                       | LOW DEFECT DENSITY SILICON HAVING A VACANCY<br>DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION<br>INDUCED STACKING FAULTS |
| MEMC2960.9                | 5143     | US-2005-0150445-A1<br>7/14/2005   | 11/03/5,987<br>12/7/2004   | MEMC Electronic<br>Materials, Inc. | Division of 10/394,629<br>recorded at<br>012789/0747  |                       | LOW DEFECT DENSITY SILICON HAVING A VACANCY<br>DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION<br>INDUCED STACKING FAULTS |
| MEMC2970.1                | 4314     | US-2003-0061905-A1<br>4/3/2003    | 10/25/6,58<br>9/27/2002    | MEMC Electronic<br>Materials, Inc. | 013578/0951   |                       | SINGLE CRYSTAL SILICON INGOT HAVING A HIGH ARSENIC<br>CONCENTRATION  |
| MEMC2984.10               | 3201     | US-2005-02255671-A1<br>11/17/2005 | 11/17/4,908<br>7/5/2005    | MEMC Electronic<br>Materials, Inc. | Division of 10/177,444<br>recorded at<br>01318/0922   |                       | PROCESS FOR PRODUCING SILICON ON INSULATOR<br>STRUCTURE HAVING INTRINSIC GROWTH BY ION<br>IMPLANTATION                   |
| MEMC2984.2                | 5976     | US-2003-0008435-A1<br>1/9/2003    | 10/17/7,444<br>6/21/2002   | MEMC Electronic<br>Materials, Inc. | 01318/0922  |                       | SILICON ON INSULATOR STRUCTURE HAVING AN EPITAXIAL<br>LAYER AND INTRINSIC GROWTH   |
| MEMC2992                  | 2873     | US-2003-0068869-A1<br>4/10/2003   | 09/682,677<br>10/4/2001    | MEMC Electronic<br>Materials, Inc. | 012328/0298   |                       | POLISHING APPARATUS, POLISHING HEAD AND METHOD   |
| MEMC3004.10               | 2878     | US-2005-00483017-A1<br>3/3/2005   | 10/19/63,340<br>10/12/2004 | MEMC Electronic<br>Materials, Inc. | Division of 10/063,340<br>recorded at<br>013923/0124  |                       | PROCESS FOR MAKING SILICON WAFERS WITH STABILIZED<br>OXYGEN PRECIPITATE NUCLEATION CENTERS                               |
| MEMC3005.3                | 1197     | US-2003-0118333-A1<br>6/24/2004   | 10/328,481<br>12/23/2002   | MEMC Electronic<br>Materials, Inc. | 013923/0124<br>2004/0118333                           |                       | SILICON WAFERS WITH STABILIZED OXYGEN PRECIPITATE<br>NUCLEATION CENTERS AND PROCESS FOR MAKING THE<br>SAME               |
| MEMC3004.2                | 8328     | US-2004-0118333-A1<br>7/24/2003   | 10/699,038<br>10/31/2003   | MEMC Electronic<br>Materials, Inc. | 013923/0124<br>2004/0118333                           |                       | PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING<br>CRUCIBLE ROTATION TO CONTROL TEMPERATURE<br>GRADIENT               |
| MEMC3007                  | 2404     | US-2004-02255847-A1<br>12/23/2004 | 10/445,548<br>6/19/2003    | MEMC Electronic<br>Materials, Inc. | 013911/0117   |                       | LIQUID SEALING SYSTEM FOR A CRYSTAL PULLER   |
| 28744107<br>(MEMC3011.1)  | 6422     | US-2003-0192409-A1<br>10/16/2003  | 10/27/7,660<br>10/22/2002  | MEMC Electronic<br>Materials, Inc. | 2003/0192469  |                       | PROCESS FOR CONTROLLING DENUDATION DEPTH IN AN<br>IDEAL OXYGEN PRECIPITATING SILICON WAFER                               |
| 28744118<br>(MEMC3035.1)  | 5409     | US-2004-011227-A1<br>6/17/2004    | 10/705,813<br>1/10/2003    | MEMC Electronic<br>Materials, Inc. | 2004/0112277  |                       | CRYSTAL PULLER AND METHOD FOR GROWING A<br>MONOCRISTALLINE INGOT   |
| MEMC3043                  | 3340     |                                   | 08/348,695<br>1/13/1994    | 5,668,045<br>9,161,997             | MEMC Electronic<br>Materials, Inc.                    | 90732/0330            | PROCESS FOR STRIPPING OUTER EDGE OF BESOI WAFERS   |